100V N-Channel MOSFETs

PDH0980

General Description

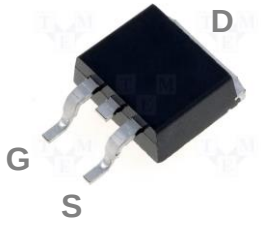
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

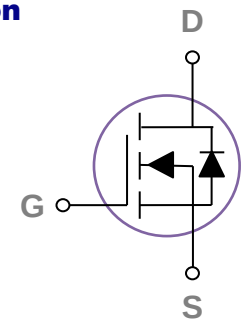
BVDSS	RDSON	ID
100V	4.2mΩ	150A

Features

- *100V,150A, RDS(ON) =4.2mΩ@VGS = 10V*
- *Improved dv/dt capability*
- *Fast switching*
- *100% EAS Guaranteed*
- *Green Device Available*

TO263 Pin Configuration





Applications

- *Networking*
- *Load Switch*
- *LED applications*
- *Quick Charger*

Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	+20/-12	V
I_D	Drain Current – Continuous (T_C=25℃)	150	A
	Drain Current – Continuous (T_C=100℃)	95	A
I_{DM}	Drain Current – Pulsed[1]	600	A
EAS	Single Pulse Avalanche Energy[2]	378	mJ
IAS	Single Pulse Avalanche Current[2]	87	A
P_D	Power Dissipation (T_C=25℃)	275	W
	Power Dissipation – Derate above 25℃	2.22	W/℃
T_{STG}	Storage Temperature Range	-50 to 150	℃
T_J	Operating Junction Temperature Range	-50 to 150	℃

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	62	℃/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	0.45	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=100V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=80V , V_{GS}=0V , T_J=85℃	---	---	10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=20V , V_{DS}=0V	---	---	100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V , I_D=20A	---	3.5	4.2	mΩ
		V_{GS}=4.5V , I_D=15A	---	4.5	6.0	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	1.8	2.5	V
gfs	Forward Transconductance	V_{DS}=10V , I_D=3A	---	20	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[3,4]	V_{DS}=80V , V_{GS}=10V , I_D=10A	---	110	165	nC
Q_{gs}	Gate-Source Charge[3,4]		---	11.5	18	
Q_{gd}	Gate-Drain Charge[3,4]		---	28	42	
$T_{d(on)}$	Turn-On Delay Time[3,4]	V_{DD}=50V , V_{GS}=10V , R_G=6Ω I_D=1A	---	23	46	ns
T_r	Rise Time[3,4]		---	32	64	
$T_{d(off)}$	Turn-Off Delay Time[3,4]		---	157	320	
T_f	Fall Time[3,4]		---	115	230	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , F=1MHz	---	6680	13300	pF
C_{oss}	Output Capacitance		---	1690	3380	
C_{rss}	Reverse Transfer Capacitance		---	78	156	
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	1.9	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G=V_D=0V , Force Current	---	---	150	A
I_{SM}	Pulsed Source Current		---	---	300	A
V_{SD}	Diode Forward Voltage	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V
t_{rr}	Reverse Recovery Time	V_{GS}=0V,I_S=10A , di/dt=100A/μs T_J=25℃	---	72	---	ns
Q_{rr}	Reverse Recovery Charge		---	162	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=87A.,R_G=25Ω,Starting T_J=25℃.
3. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
4. Essentially independent of operating temperature.

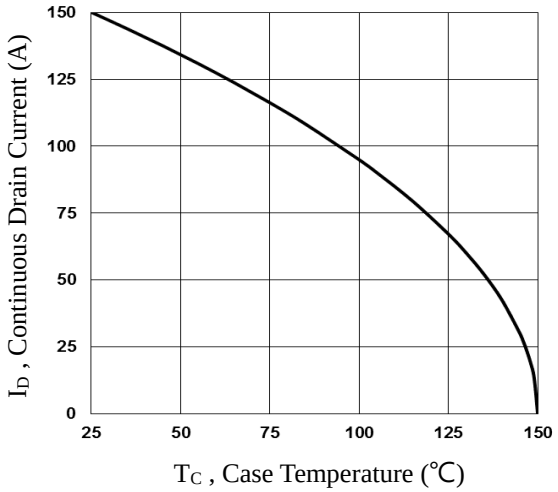


Fig.1 Continuous Drain Current vs. T_C

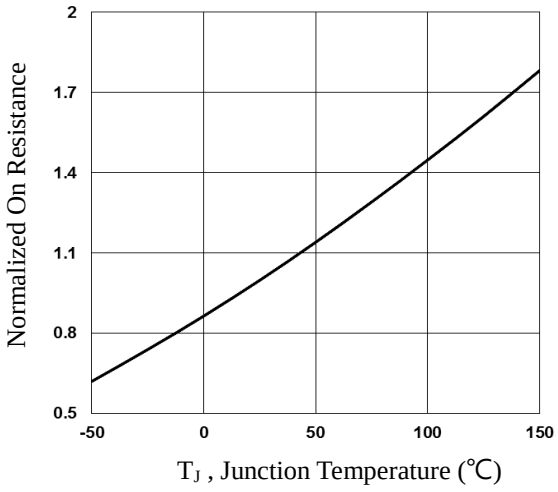


Fig.2 Normalized RDSON vs. T_J

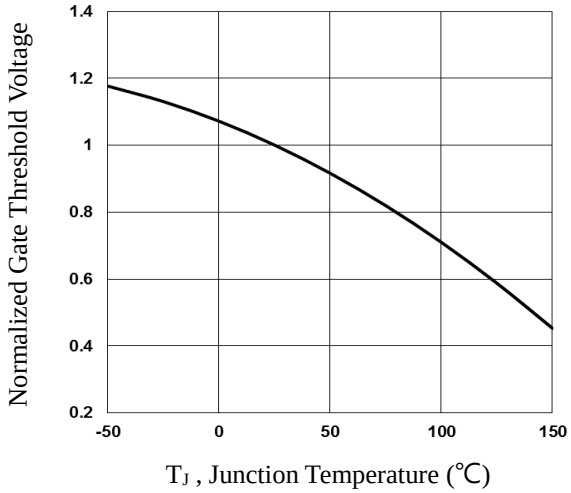


Fig.3 Normalized Vth vs. T_J

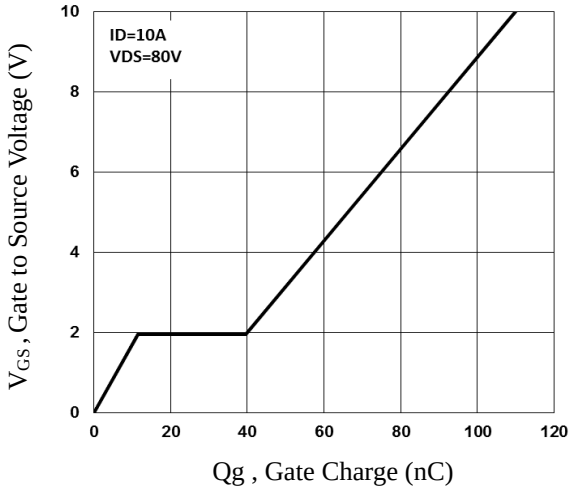


Fig.4 Gate Charge Characteristics

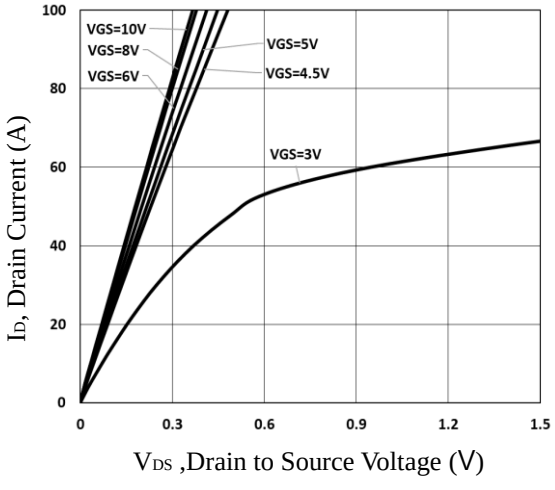


Fig.5 Typical Output Characteristics

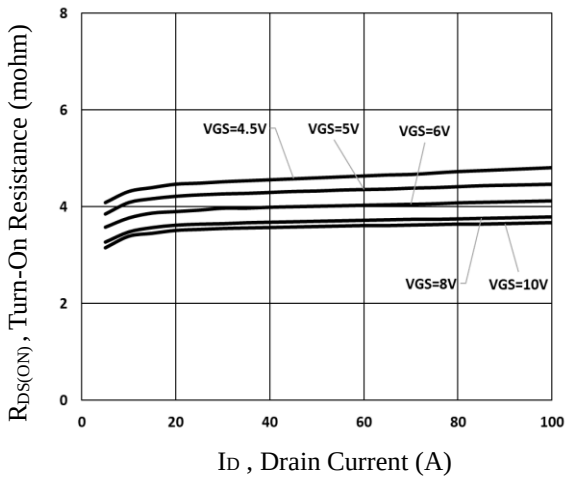


Fig.6 Turn-On Resistance vs. I_D

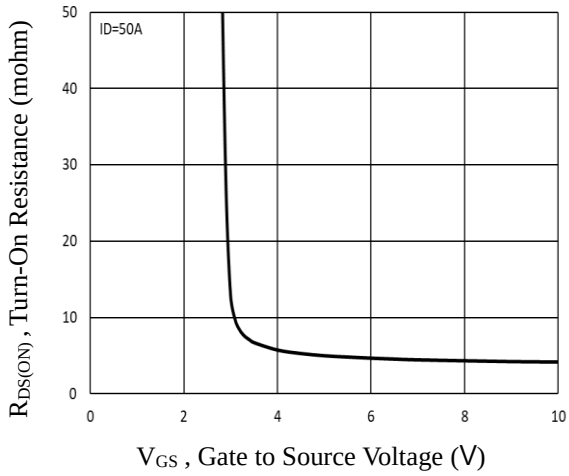


Fig.7 RDSON vs. VGS

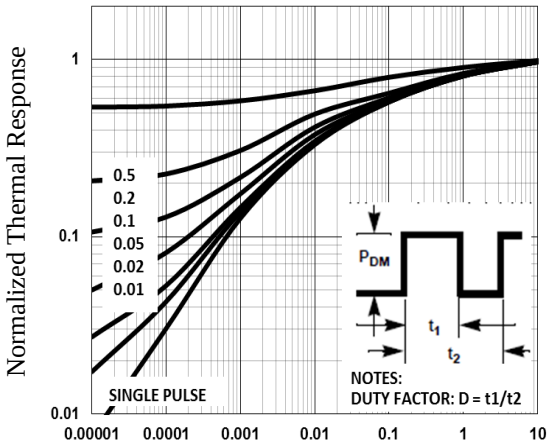


Fig.8 Normalized Transient Impedance

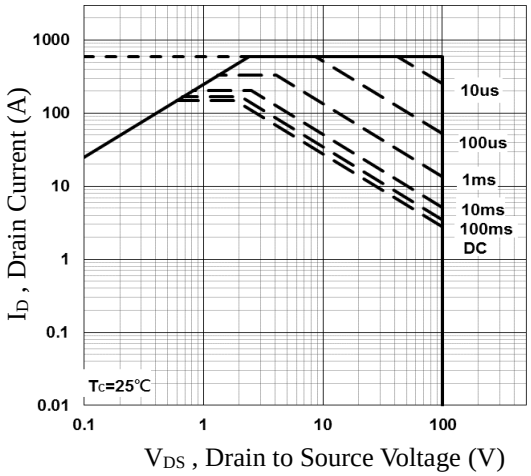


Fig.9 Maximum Safe Operation Area

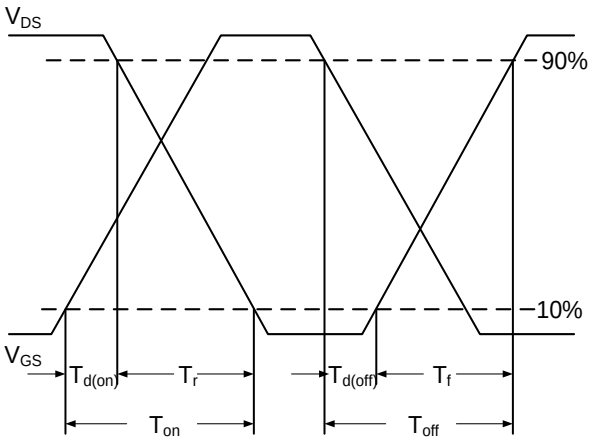


Fig.10 Switching Time Waveform

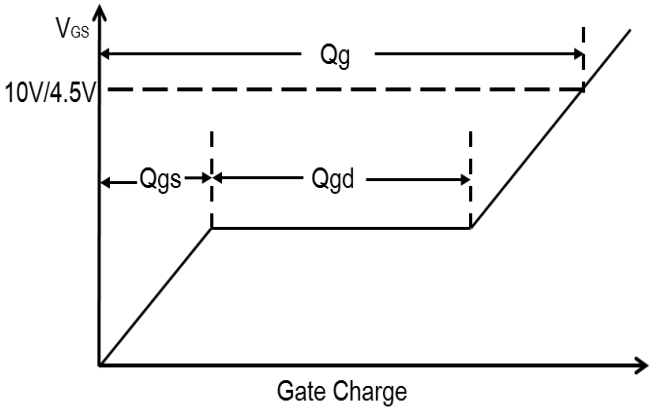


Fig.11 Gate Charge Waveform

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